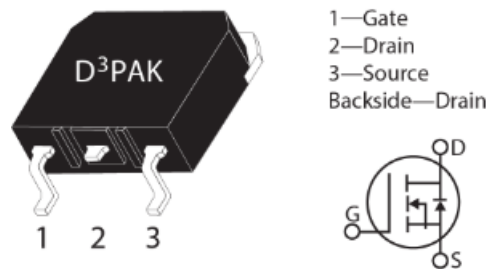


MSC750SMA170S Silicon Carbide N-Channel Power MOSFET

Product Overview

The silicon carbide (SiC) power MOSFET product line from Microsemi increases the performance over silicon MOSFET and silicon IGBT solutions while lowering the total cost of ownership for high-voltage applications. The MSC750SMA170S device is a 1700 V, 750 mΩ SiC MOSFET in a TO-268 (D3PAK) package.



Features

The following are key features of the MSC750SMA170S device:

- Low capacitances and low gate charge
- Fast switching speed due to low internal gate resistance (ESR)
- Stable operation at high junction temperature, $T_{J(max)} = 175\text{ }^{\circ}\text{C}$
- Fast and reliable body diode
- Superior avalanche ruggedness
- RoHS compliant

Benefits

The following are benefits of the MSC750SMA170S device:

- High efficiency to enable lighter, more compact system
- Simple to drive and easy to parallel
- Improved thermal capabilities and lower switching losses
- Eliminates the need for external freewheeling diode
- Lower system cost of ownership

Applications

The MSC750SMA170S device is designed for the following applications:

- PV inverter, converter, and industrial motor drives
- Smart grid transmission and distribution
- Induction heating and welding
- H/EV powertrain and EV charger
- Power supply and distribution

Device Specifications

This section shows the specifications of the MSC750SMA170S device.

Absolute Maximum Ratings

The following table shows the absolute maximum ratings of the MSC750SMA170S device.

Table 1 • Absolute Maximum Ratings

Symbol	Characteristic	Ratings	Unit
V_{DS}	Drain source voltage	1700	V
I_D	Continuous drain current at $T_C = 25\text{ }^{\circ}\text{C}$	6	A
	Continuous drain current at $T_C = 100\text{ }^{\circ}\text{C}$	4	
	Pulsed drain current ¹	12	
V_{GS}	Gate-source voltage	23 to -10	V
P_D	Total power dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	63	W
	Linear derating factor	0.42	W/ $^{\circ}\text{C}$

Note:

1. Repetitive rating: pulse width and case temperature limited by maximum junction temperature.

The following table shows the thermal and mechanical characteristics of the MSC750SMA170S device.

Table 2 • Thermal and Mechanical Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction-to-case thermal resistance		1.6	2.39	$^{\circ}\text{C}/\text{W}$
T_J	Operating junction temperature	-55		175	$^{\circ}\text{C}$
T_{STG}	Storage temperature	-55		150	
T_L	Soldering temperature for 10 seconds (1.6 mm from case)			300	
Wt	Package weight		0.14		oz
			4.0		g

Electrical Performance

The following table shows the static characteristics of the MSC750SMA170S device. $T_J = 25^\circ\text{C}$ unless otherwise specified.

Table 3 • Static Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}, I_D = 100\text{ }\mu\text{A}$	1700			V
$R_{DS(on)}$	Drain-source on resistance ¹	$V_{GS} = 20\text{ V}, I_D = 2.5\text{ A}$		750	940	m Ω
$V_{GS(th)}$	Gate-source threshold voltage	$V_{GS} = V_{DS}, I_D = 100\text{ }\mu\text{A}$	1.9	3.25		V
$\Delta V_{GS(th)}/\Delta T_J$	Threshold voltage coefficient	$V_{GS} = V_{DS}, I_D = 100\text{ }\mu\text{A}$		-5.7		mV/ $^\circ\text{C}$
I_{DSS}	Zero gate voltage drain current	$V_{DS} = 1700\text{ V}, V_{GS} = 0\text{ V}$			100	μA
		$V_{DS} = 1700\text{ V}, V_{GS} = 0\text{ V}$ $T_J = 125^\circ\text{C}$			500	
I_{GSS}	Gate-source leakage current	$V_{GS} = 20\text{ V}/-10\text{ V}$			± 100	nA

Note:

1. Pulse test: pulse width < 380 μs , duty cycle < 2%.

The following table shows the dynamic characteristics of the MSC750SMA170S device. $T_J = 25^\circ\text{C}$ unless otherwise specified.

Table 4 • Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input capacitance	$V_{GS} = 0\text{ V}, V_{DD} = 1000\text{ V}$ $V_{AC} = 25\text{ mV}, f = 1\text{ MHz}$		184		pF
C_{rss}	Reverse transfer capacitance			2		
C_{oss}	Output capacitance			14		
Q_g	Total gate charge	$V_{GS} = -5\text{ V}/20\text{ V}, V_{DD} = 850\text{ V}$ $I_D = 2.5\text{ A}$		11		nC
Q_{gs}	Gate-source charge			2.9		
Q_{gd}	Gate-drain charge			2.1		
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 1200\text{ V}, V_{GS} = -5\text{ V}/20\text{ V}$ $I_D = 5\text{ A}, R_{G(ext)} = 8\text{ }\Omega$, Freewheeling diode = MSC750SMA170S ($V_g = -5\text{ V}$)		13		ns
t_f	Voltage fall time			12		
$t_{d(off)}$	Turn-off delay time			7		

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
t_r	Voltage rise time			8		
E_{on}	Turn-on switching energy			107		μJ
E_{off}	Turn-off switching energy			17		
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 1200\text{ V}$, $V_{GS} = -5\text{ V}/20\text{ V}$ $I_D = 5\text{ A}$, $R_{G(ext)} = 8\ \Omega$, $T_J = 150\text{ }^\circ\text{C}$ Freewheeling diode = MSC750SMA170S		13		ns
t_f	Voltage fall time			12		
$t_{d(off)}$	Turn-off delay time			7		
t_r	Voltage rise time			8		
E_{on}	Turn-on switching energy			185		μJ
E_{off}	Turn-off switching energy			20		
ESR	Equivalent series resistance	$f = 1\text{ MHz}$, 25 mV, drain short		2.89		Ω
SCWT	Short circuit withstand time	$V_{DS} = 1200\text{ V}$, $V_{GS} = 20\text{ V}$		2.5		μs
E_{AS}	Avalanche energy, single pulse	$V_{DS} = 150\text{ V}$, $V_{GS} = 20\text{ V}$, $I_D = 2.5\text{ A}$		360		mJ

The following table shows the body diode characteristics of the MSC750SMA170S device. $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified.

Table 5 • Body Diode Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{SD}	Diode forward voltage	$I_{SD} = 2.5\text{ A}$, $V_{GS} = 0\text{ V}$		3.7		V
		$I_{SD} = 2.5\text{ A}$, $V_{GS} = -5\text{ V}$		3.9		V
t_{rr}	Reverse recovery time	$I_{SD} = 5\text{ A}$, $V_{GS} = -5\text{ V}$, $V_{DD} = 1200\text{ V}$, $dI/dt = -2000\text{ A}/\mu s$ Drive $R_g = 8\ \Omega$		18		ns
Q_{rr}	Reverse recovery charge			120		nC
I_{RRM}	Reverse recovery current			3.0		A

Typical Performance Curves

This section shows the typical performance curves of the MSC750SMA170S device.

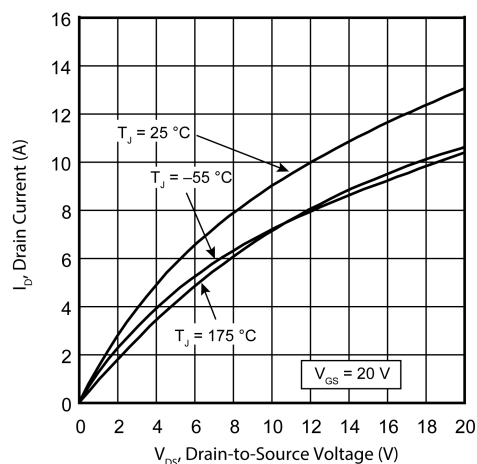


Figure 1 • Drain Current vs. V_{DS}

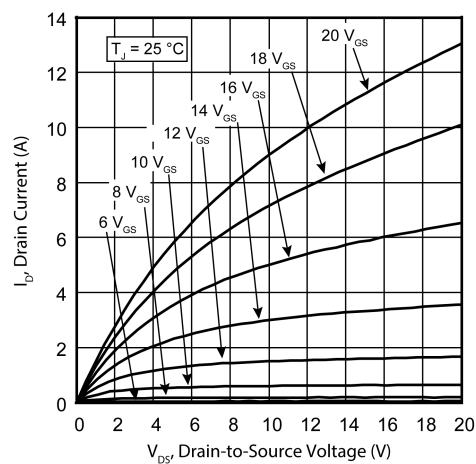


Figure 2 • Drain Current vs. V_{DS}

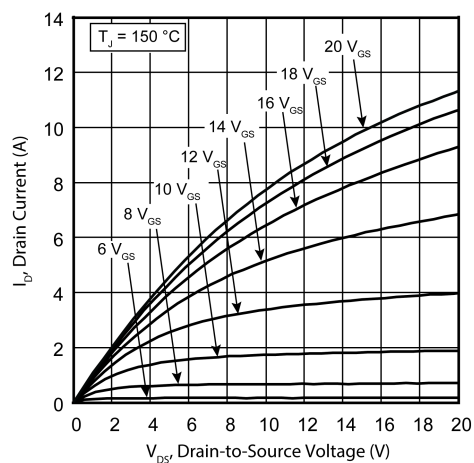


Figure 3 • Drain Current vs. V_{DS}

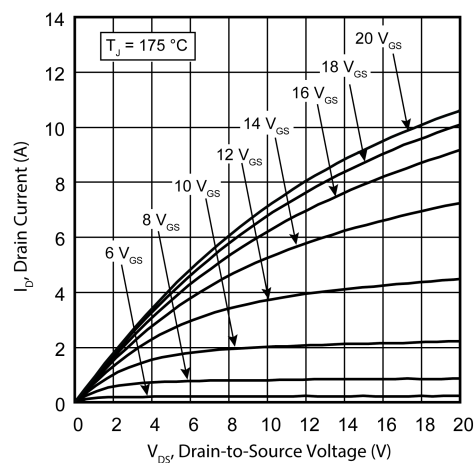


Figure 4 • Drain Current vs. V_{DS}

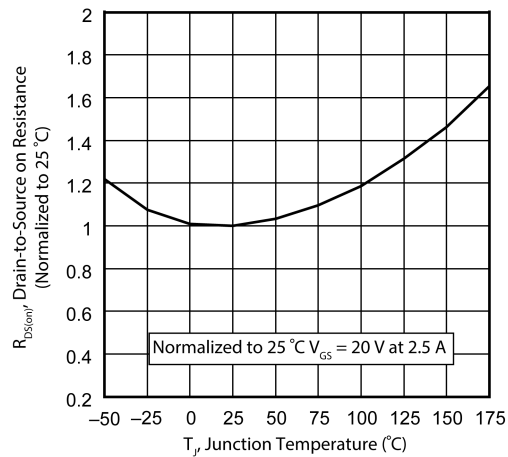
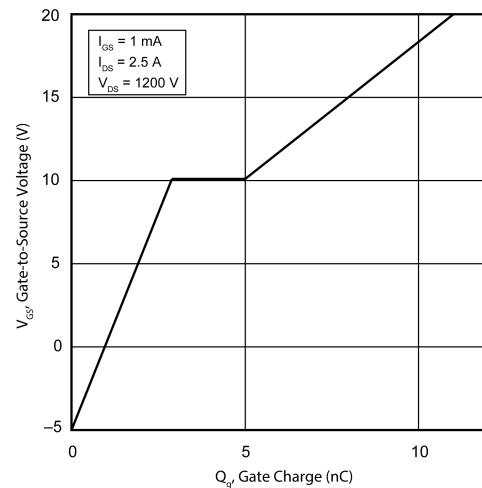
Figure 5 • $R_{DS(on)}$ vs. Junction Temperature

Figure 6 • Gate Charge Characteristics

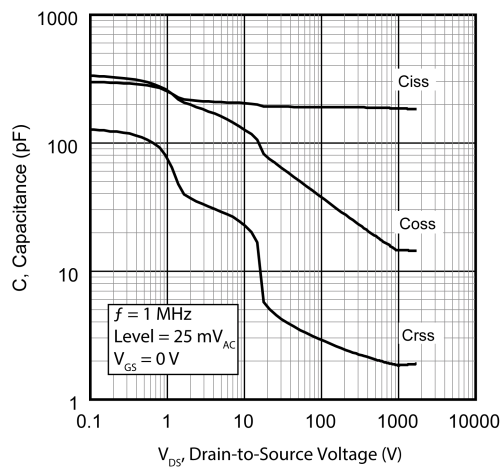
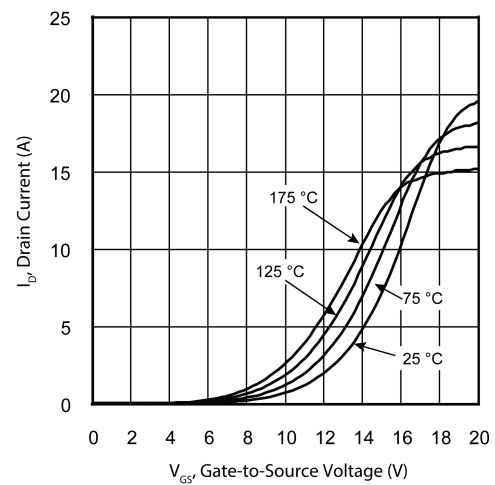
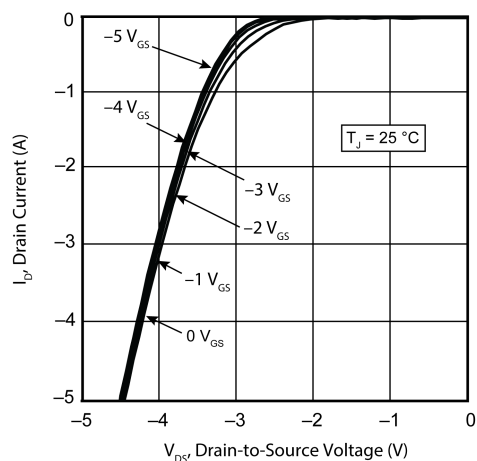
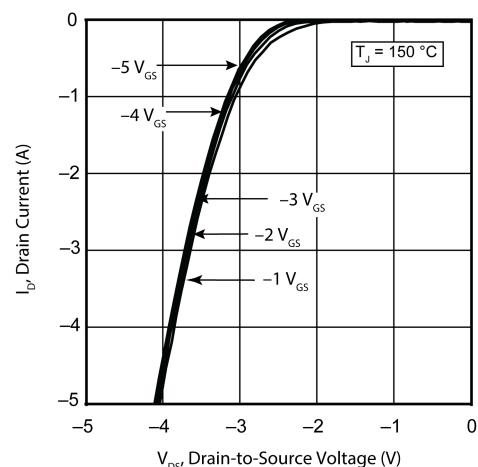
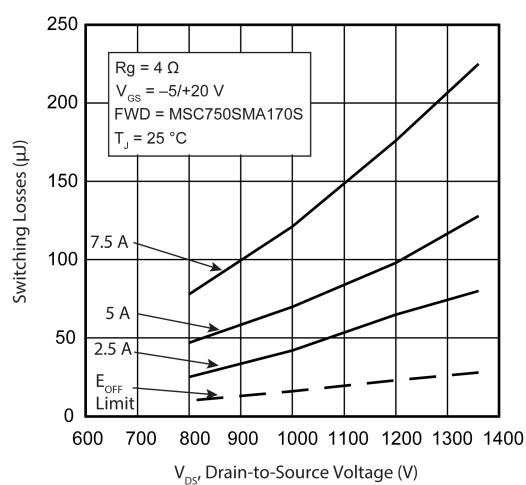
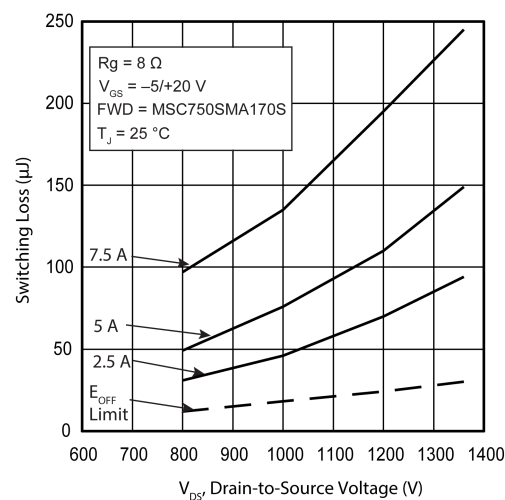


Figure 7 • Capacitance vs. Drain-to-Source Voltage

Figure 8 • I_D vs. Gate-to-Source Voltage

Figure 9 • I_D vs. V_{DS} 3rd Quadrant ConductionFigure 10 • I_D vs. V_{DS} 3rd Quadrant ConductionFigure 11 • Switching Energy vs. V_{DS} & I_D Figure 12 • Switching Energy vs. V_{DS} & I_D

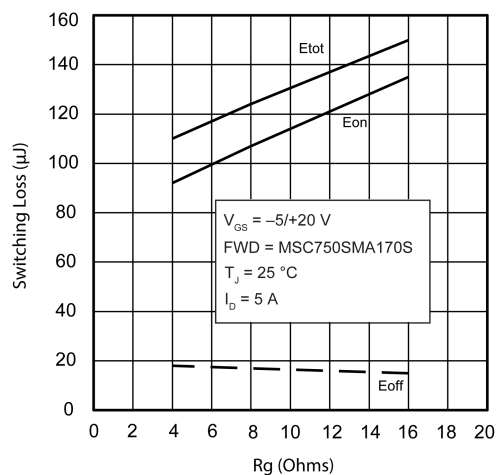


Figure 13 • Switching Energy vs. Rg

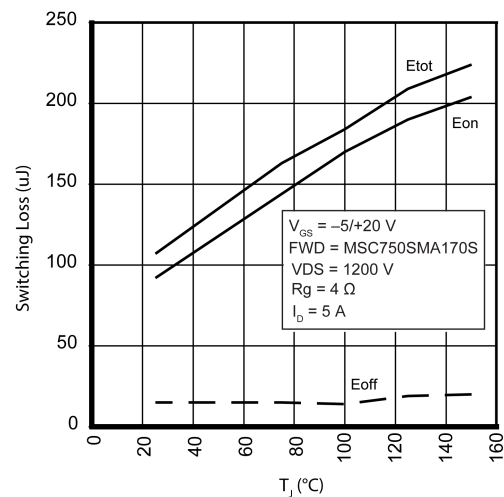


Figure 14 • Switching Energy vs. Temperature

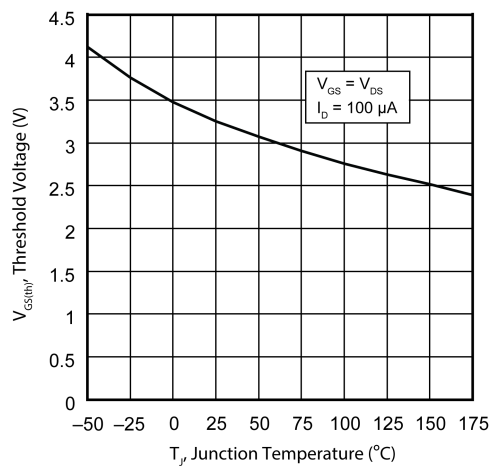


Figure 15 • Threshold Voltage vs. Junction Temp.

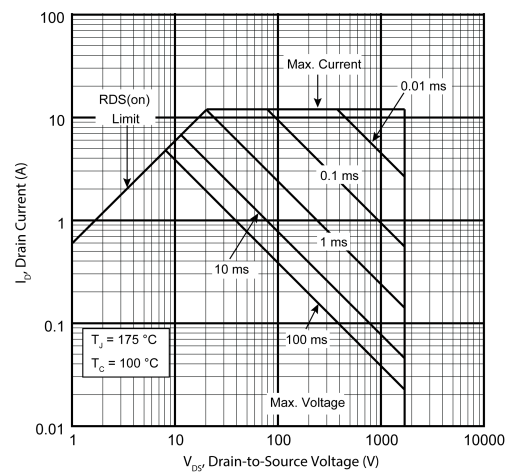


Figure 16 • Forward Safe Operating Area

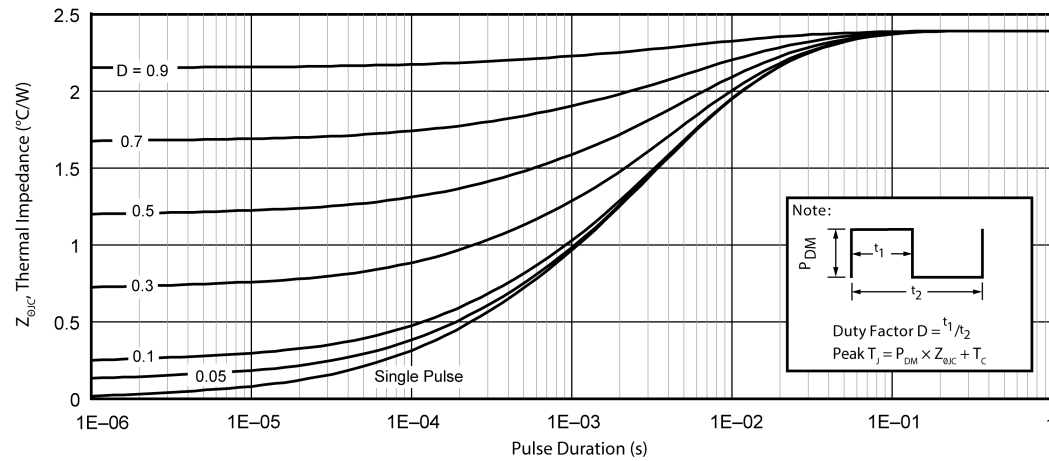


Figure 17 • Maximum Transient Thermal Impedance

Package Specification

This section shows the package specification of the MSC750SMA170S device.

Package Outline Drawing

The following figure illustrates the TO-268 package outline of the MSC750SMA170S device.

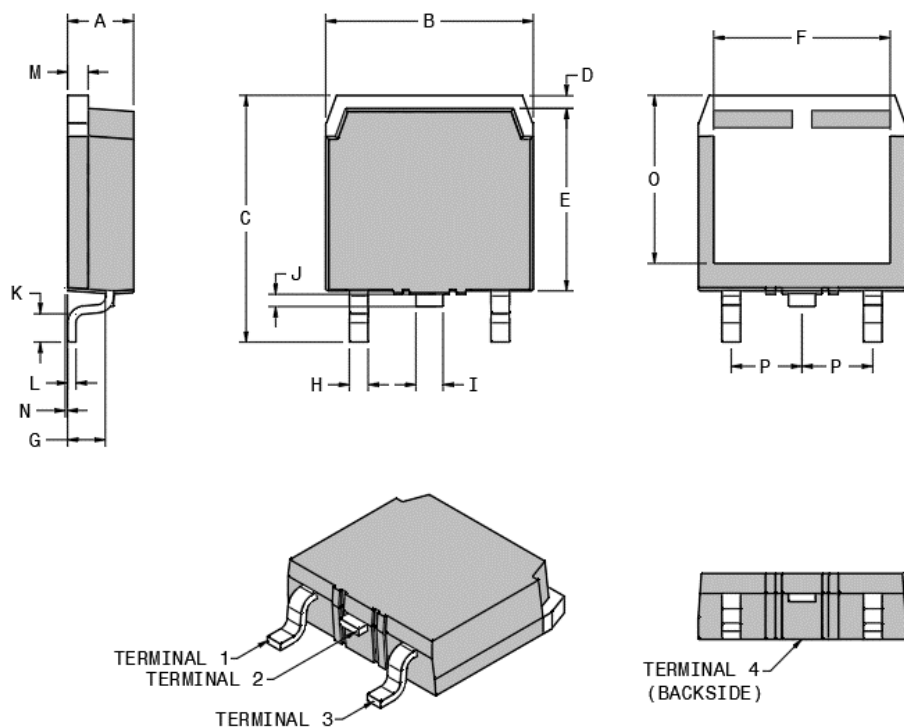


Figure 18 • Package Outline Drawing

The following table shows the TO-268 dimensions and should be used in conjunction with the package outline drawing.

Table 6 • TO-268 Dimensions

Symbol	Min (mm)	Max (mm)	Min (in.)	Max (in.)
A	4.90	5.10	0.193	0.201
B	15.85	16.20	0.624	0.638
C	18.70	19.10	0.736	0.752
D	1.00	1.25	0.039	0.049
E	13.80	14.00	0.543	0.551
F	13.30	13.60	0.524	0.535

Symbol	Min (mm)	Max (mm)	Min (in.)	Max (in.)
G	2.70	2.90	0.106	0.114
H	1.15	1.45	0.045	0.057
I	1.95	2.21	0.077	0.087
J	0.94	1.40	0.037	0.055
K	2.40	2.70	0.094	0.106
L	0.40	0.60	0.016	0.024
M	1.45	1.60	0.057	0.063
N	0.00	0.18	0.000	0.007
O	12.40	12.70	0.488	0.500
P	5.45 BSC (nom.)		0.215 BSC (nom.)	
Terminal 1	Gate			
Terminal 2	Drain			
Terminal 3	Source			
Terminal 4	Drain			

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